

## AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): An HF power device in an HF transistor, comprising:

- a first semiconductor layer as a first conductive type;

- a second semiconductor layer formed on the first semiconductor layer;

- a field area having a trench structure formed in the second semiconductor layer;

- a gate electrode formed on the second semiconductor layer;

- a channel layer as a second conductive type laterally diffused from the field area to a width containing both sides of the gate electrode in the second semiconductor layer;

- a source area as the second conductive type formed within the channel layer between one side of the gate electrode and the field area;

- a drain area as the second conductive type formed in the second semiconductor layer with a given interval from another side of the gate electrode;

- a sinker as the first conductive type provided as a column shape of a plurality of trenches structure for dividing into two source areas and directly connecting the source area and the first semiconductor layer by piercing through the source area and the second semiconductor layer, ~~and connected to the first semiconductor layer;~~

- an LDD area as the second conductive type formed on the surface of the semiconductor layer between the drain area and the gate electrode;

- first metal electrode contacted with the source area and electrically connected to the second semiconductor layer through the sinker; and

- second metal electrode coupled with the drain area.

Claim 2 (Currently Amended): The device of claim 1, wherein said sinker is provided as the plurality of trenches structure doped with impurity of the first conductive type on the neighborhood thereof, said plurality of trenches structure having a burying of polysilicon film based on the first conductive type thereinto.

Claim 3 (Canceled):

Claim 4 (Currently Amended): The device of claim 1, wherein said field area is any one among an oxide film grown in the trench, an oxide film gained by performing a

covering on the plurality of trenches and then by executing a burying thereinto through a use of a chemical mechanical polishing, and a thermal oxide film gained by performing a thermal oxidation for the plurality of trenches.

Claims 5-11 (Canceled)

Claim 12 (New): An HF power device in an HF transistor, comprising:

- a first semiconductor layer as a first conductive type;
- a second semiconductor layer formed on the first semiconductor layer;
- a channel layer as a second conductive type laterally diffused from a field area to a width containing both sides of a gate electrode in the second semiconductor layer;
- a source area as the second conductive type formed within the channel layer between one side of the gate electrode and the field area; and
- a sinker as the first conductive type provided as a column shape of a plurality of trenches for dividing into two source areas and directly connecting the source area and the first semiconductor layer by piercing through the source area and the second semiconductor layer.